

TO-92 Plastic-Encapsulate Transistors

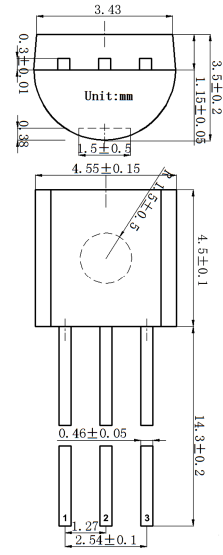
FEATURES

- Complementary to S9013
- Excellent linearity
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector Base Voltage	-40	V
V _{CE0}	Collector Emitter Voltage	-25	V
V _{EB0}	Emitter Base Voltage	-5	V
I _c	Collector Current	-500	mA
P _c	Collector Power Dissipation	625	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{(BR)CB0}	Collector-base breakdown voltage	I _c = -100μA, I _E = 0	-40			V
V _{(BR)CE0}	Collector-emitter breakdown voltage	I _c = -1mA, I _B = 0	-25			V
V _{(BR)EB0}	Emitter-base breakdown voltage	I _E = -100μA, I _c = 0	-5			V
I _{cBO}	Collector cut-off current	V _{CB} = -40V, I _E = 0			-100	nA
I _{CE0}	Collector cut-off current	V _{CE} = -20V, I _B = 0			-100	nA
I _{EBO}	Emitter cut-off current	V _{EB} = -5V, I _c = 0			-100	nA
h _{FE(1)}	DC current gain	V _{CE} = -1V, I _c = -50mA	200		300	
V _{CE(sat)}	Collector-emitter saturation voltage	I _c = -500mA, I _B = -50mA			-0.6	V
V _{BE(sat)}	Base-emitter saturation voltage	I _c = -500mA, I _B = -50mA			-1.2	V
f _T	Transition frequency	V _{CE} = -6V, I _c = -20mA, f = 30MHz	150			MHz

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

